Achim Trampert

List of Publications by Year in Descending Order

261 papers	7,969 citations	43 h-index	79 g-index
265 ext. papers	8,426 ext. citations	3.8 avg, IF	5.53 L-index

#	Paper	IF	Citations
261	SnO/β-Ga2O3 heterojunction field-effect transistors and vertical p-i-n diodes. *Applied Physics Letters*, **2022**, 120, 112110	3.4	4
260	Drastic Effect of Sequential Deposition Resulting from Flux Directionality on the Luminescence Efficiency of Nanowire Shells. *ACS Applied Materials & Interfaces*, **2021**, 13, 50220-50227	9.5	1
259	Application of electron tomography for comprehensive determination of III-V interface properties. *Ultramicroscopy*, **2021**, 224, 113261	3.1	0
258	In Situ Transmission Electron Microscopy of Disorder–Order Transition in Epitaxially Stabilized FeGe2. *Journal of Physical Chemistry C*, **2021**, 125, 2779-2784	3.8	
257	Nucleation Chronology and Electronic Properties of InAs1−ySbxPy Graded Composition Quantum Dots Grown on an InAs(100) Substrate. *ACS Applied Electronic Materials*, **2020**, 2, 646-650	4	2
256	Interfacial resistance switching characteristics in metal-chalcogenide junctions using Bi–Cu–Se, Bi–Ag–Se, and Sb–Cu–Te alloys. *Journal of Alloys and Compounds*, **2020**, 824, 153880	5.7	2
255	Coaxial GaAs/(In,Ga)As Dot-in-a-Well Nanowire Heterostructures for Electrically Driven Infrared Light Generation on Si in the Telecommunication O Band. *ACS Applied Nano Materials*, **2020**, 3, 165-174	5.6	8
254	Strategies for Analyzing Noncommon-Atom Heterovalent Interfaces: The Case of CdTe-on-InSb. *Advanced Materials Interfaces*, **2020**, 7, 1901658	4.6	9
253	Bismuth-surfactant-induced growth and structure of InAs/GaAs(110) quantum dots. *Semiconductor Science and Technology*, **2019**, 34, 105016	1.8	3
252	Impact of Bi incorporation on the evolution of microstructure during growth of low-temperature GaAs:Bi/Ga(As,Bi) layers. *Journal of Applied Physics*, **2019**, 126, 085305	2.5	4
251	Toward heterostructured transition metal hybrids with highly promoted electrochemical hydrogen evolution.. *RSC Advances*, **2019**, 9, 19924-19929	3.7	3
250	Interfacial reactions during the molecular beam epitaxy of GaN nanowires on Ti/AlO. *Nanotechnology*, **2019**, 30, 114001	3.4	9
249	Ordered arrays of defect-free GaN nanocolumns with very narrow excitonic emission line width. *Journal of Crystal Growth*, **2019**, 525, 125189	1.6	5
248	Electron Tomography of Pencil-Shaped GaN/(In,Ga)N Core-Shell Nanowires. *Nanoscale Research Letters*, **2019**, 14, 232	5	3
247	Memristive resistive switch based on spontaneous barrier creation in metal-chalcogenide junctions. *Journal Physics D: Applied Physics*, **2019**, 52, 385101	3	5
246	GaSbBi Alloys and Heterostructures: Fabrication and Properties. *Springer Series in Materials Science*, **2019**, 125-161	0.9	1
245	Molecular-beam epitaxy of GaInSbBi alloys. *Journal of Applied Physics*, **2019**, 126, 155304	2.5	3

244	Lattice matched Volmer–Weber growth of Fe3Si on GaAs(001): The influence of the growth rate. *Semiconductor Science and Technology*, **2019**, 34, 124002	1.8	1
243	In situ transmission electron microscopy of solid phase epitaxy of Ge on Fe3Si. *Semiconductor Science and Technology*, **2019**, 34, 124004	1.8	2
242	Li2SnO3 branched nano- and microstructures with intense and broadband white-light emission. *Nano Research*, **2019**, 12, 441-448	10	7
241	Excitonic Aharonov-Bohm Oscillations in Core-Shell Nanowires. *Advanced Materials*, **2019**, 31, e1805645	24	10
240	3D GaN Fins as a Versatile Platform for a-Plane-Based Devices. *Physica Status Solidi (B): Basic Research*, **2019**, 256, 1800477	1.3	3
239	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. *Applied Physics Letters*, **2018**, 112, 151905	3.4	14
238	Manifestation of axiotaxy induced by the (10.4) plane in high-temperature-grown bismuth telluride films on InP(111). *CrystEngComm*, **2018**, 20, 983-989	3.3	1
237	Phase Stability and Anisotropic Sublimation of Cubic GeSbTe Alloy Observed by In Situ Transmission Electron Microscopy. *Journal of Physical Chemistry C*, **2018**, 122, 2968-2974	3.8	7
236	Crystal-Phase Quantum Wires: One-Dimensional Heterostructures with Atomically Flat Interfaces. *Nano Letters*, **2018**, 18, 247-254	11.5	3
235	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. *Acta Materialia*, **2018**, 143, 121-129	8.4	7
234	Transmission electron microscopy of Ga(Sb, Bi)/GaSb quantum wells with varying Bi content and quantum well thickness. *Semiconductor Science and Technology*, **2018**, 33, 094006	1.8	4
233	Growth mode evolution during (100)-oriented β-Ga2O3 homoepitaxy. *Nanotechnology*, **2018**, 29, 395705	3.4	8
232	Ordered structure of FeGe2 formed during solid-phase epitaxy. *Physical Review Materials*, **2018**, 2,	3.2	3
231	Thermal expansion of single-crystalline β-Ga2O3 from RT to 1200 K studied by synchrotron-based high resolution x-ray diffraction. *Applied Physics Letters*, **2018**, 113, 182102	3.4	7
230	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. *Scripta Materialia*, **2017**, 132, 5-8	5.6	7
229	Growth of GaP and AlGaP on GaP(1 1 1)B using gas-source molecular-beam-epitaxy. *Journal of Crystal Growth*, **2017**, 477, 91-96	1.6	1
228	Tailoring of microstructure and optoelectronic properties of Aluminum doped Zinc Oxide changing gun tilt. *Materials Science in Semiconductor Processing*, **2017**, 63, 115-121	4.3	8
227	Structure and Composition of Isolated Core-Shell (In,Ga)N/GaN Rods Based on Nanofocus X-Ray Diffraction and Scanning Transmission Electron Microscopy. *Physical Review Applied*, **2017**, 7,	4.3	11

226	Morphological and chemical instabilities of nitrogen delta-doped GaAs/(Al, Ga)As quantum wells. *Applied Physics Letters*, **2017**, 110, 201906	3.4	3
225	GaSbBi/GaSb quantum well laser diodes. *Applied Physics Letters*, **2017**, 110, 222106	3.4	40
224	Toward edges-rich MoS2 layers via chemical liquid exfoliation triggering distinctive magnetism. *Materials Research Letters*, **2017**, 5, 267-275	7.4	12
223	Growth of Fe3Si/Ge/Fe3Si trilayers on GaAs(001) using solid-phase epitaxy. *Applied Physics Letters*, **2017**, 110, 102103	3.4	16
222	Supernormal hardness increase of dilute Ga(As, N) thin films. *Journal of Applied Physics*, **2017**, 121, 095105	2.5	1
221	Polarity-Induced Selective Area Epitaxy of GaN Nanowires. *Nano Letters*, **2017**, 17, 63-70	11.5	14
220	Anomalous Strain Relaxation in Core-Shell Nanowire Heterostructures via Simultaneous Coherent and Incoherent Growth. *Nano Letters*, **2017**, 17, 136-142	11.5	31
219	Phase formation and strain relaxation of Ga2O3 on c-plane and a-plane sapphire substrates as studied by synchrotron-based x-ray diffraction. *Applied Physics Letters*, **2017**, 111, 162104	3.4	42
218	Study of 3D-growth conditions for selective area MOVPE of high aspect ratio GaN fins with non-polar vertical sidewalls. *Journal of Crystal Growth*, **2017**, 476, 90-98	1.6	12
217	Continuous tuning of two-section, single-mode terahertz quantum-cascade lasers by fiber-coupled, near-infrared illumination. *AIP Advances*, **2017**, 7, 055201	1.5	5
216	Strain Driven Shape Evolution of Stacked (In,Ga)N Quantum Disks Embedded in GaN Nanowires. *Nano Letters*, **2017**, 17, 4654-4660	11.5	5
215	Molecular Beam Epitaxy of GaN Nanowires on Epitaxial Graphene. *Nano Letters*, **2017**, 17, 5213-5221	11.5	60
214	Metal-Semiconductor Phase-Transition in WSe Te Monolayer. *Advanced Materials*, **2017**, 29, 1603991	24	88
213	Liquid-solid phase transition of Ge-Sb-Te alloy observed by in-situ transmission electron microscopy. *Ultramicroscopy*, **2017**, 178, 27-32	3.1	3
212	The Role of Epitaxial Strain on the Spontaneous Formation of Bi-Rich Nanostructures in Ga(As,Bi) Epilayers and Quantum Wells. *Nanoscience and Nanotechnology Letters*, **2017**, 9, 1132-1138	0.8	5
211	Nature of excitons bound to inversion domain boundaries: Origin of the 3.45-eV luminescence lines in spontaneously formed GaN nanowires on Si(111). *Physical Review B*, **2016**, 94,	3.3	10
210	Nanofocus x-ray diffraction and cathodoluminescence investigations into individual core-shell (In,Ga)N/GaN rod light-emitting diodes. *Nanotechnology*, **2016**, 27, 325707	3.4	16
209	Observation of Dielectrically Confined Excitons in Ultrathin GaN Nanowires up to Room Temperature. *Nano Letters*, **2016**, 16, 973-80	11.5	27

208	Structural properties of Co2TiSi films on GaAs(001). *Journal of Applied Physics*, **2016**, 120, 225304	2.5	
207	Counterintuitive strain distribution in axial (In,Ga)N/GaN nanowires. *Applied Physics Letters*, **2016**, 108, 032103	3.4	14
206	Bowing effect in elastic constants of dilute Ga(As,N) alloys. *Applied Physics Letters*, **2016**, 108, 183106	3.4	2
205	Molecular beam epitaxy of single crystalline GaN nanowires on a flexible Ti foil. *Applied Physics Letters*, **2016**, 108, 202101	3.4	69
204	Strain dynamics during La2O3/Lu2O3 superlattice and alloy formation. *Journal of Applied Physics*, **2016**, 119, 215301	2.5	1
203	Polarity in GaN and ZnO: Theory, measurement, growth, and devices. *Applied Physics Reviews*, **2016**, 3, 041303	17.3	85
202	Diffraction at GaAs/Fe3Si core/shell nanowires: The formation of nanofacets. *AIP Advances*, **2016**, 6, 055108	1.8	2
201	Exciton recombination at crystal-phase quantum rings in GaAs/InxGa1−xAs core/multishell nanowires. *Applied Physics Letters*, **2016**, 109, 082107	3.4	10
200	Growth and stability of rocksalt Zn1-xMgxO epilayers and ZnO/MgO superlattice on MgO (100) substrate by molecular beam epitaxy. *Journal of Chemical Physics*, **2016**, 144, 214704	3.9	12
199	Spontaneous formation of three-dimensionally ordered Bi-rich nanostructures within GaAs1-x Bi x /GaAs quantum wells. *Nanotechnology*, **2016**, 27, 325603	3.4	27
198	Facetted growth of Fe3Si shells around GaAs nanowires on Si(111). *Journal of Crystal Growth*, **2015**, 427, 21-23	1.6	5
197	Spontaneous formation of nanostructures by surface spinodal decomposition in GaAs1−xBix epilayers. *Journal of Applied Physics*, **2015**, 117, 185302	2.5	25
196	Interface structure and strain state of InAs nano-clusters embedded in silicon. *Acta Materialia*, **2015** , 90, 133-139	8.4	11
195	Electron tomography on nanopores embedded in epitaxial GaSb thin films. *Micron*, **2015**, 73, 54-62	2.3	8
194	Molecular beam epitaxy growth and properties of Co2TiSi thin films on GaAs(0 0 1): the effect of growth temperature. *Journal Physics D: Applied Physics*, **2015**, 48, 025003	3	4
193	Real structure of lattice matched GaAs−Fe3Si core−shell nanowires. *Journal of Crystal Growth*, **2015**, 410, 1-6	1.6	6
192	Perpendicular magnetic anisotropy in the Heusler alloy Co2TiSi/GaAs(001) hybrid structure. *AIP Advances*, **2015**, 5, 057130	1.5	4
191	Electron tomography of (In,Ga)N insertions in GaN nanocolumns grown on semi-polar (112 2) GaN templates. *APL Materials*, **2015**, 3, 036102	5.7	3

190	Detecting lateral composition modulation in dilute Ga(As,Bi) epilayers. *Nanotechnology*, **2015**, 26, 425701	3.4	15
189	Correlation among Growth Conditions, Morphology, and Optical Properties of Nanocolumnar InGaN/GaN Heterostructures Selectively Grown by Molecular Beam Epitaxy. *Crystal Growth and Design*, **2015**, 15, 2661-2666	3.5	12
188	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. *Optics Express*, **2015**, 23, 29423-33	3.3	8
187	Magnetic properties of Gd-doped GaN. *Physica Status Solidi (B): Basic Research*, **2014**, 251, 1673-1684	1.3	11
186	Coaxial multishell (In,Ga)As/GaAs nanowires for near-infrared emission on Si substrates. *Nano Letters*, **2014**, 14, 2604-9	11.5	104
185	Atomistic structure and energetics of GdN clusters in Gd-doped GaN. *Acta Materialia*, **2014**, 76, 87-93	8.4	4
184	Investigation of III-V nanowires by plan-view transmission electron microscopy: InN case study. *Microscopy and Microanalysis*, **2014**, 20, 1471-8	0.5	5
183	Formation and phase transformation of Bi-containing QD-like clusters in annealed GaAsBi. *Nanotechnology*, **2014**, 25, 205605	3.4	39
182	Observation of atomic ordering of triple-period-A and -B type in GaAsBi. *Applied Physics Letters*, **2014**, 105, 041602	3.4	31
181	Axial InAs/GaAs heterostructures on silicon in a nanowire geometry. *Nanotechnology*, **2014**, 25, 485602	3.4	1
180	Lattice-engineered Si1-xGex-buffer on Si(001) for GaP integration. *Journal of Applied Physics*, **2014**, 115, 103501	2.5	8
179	Plan-view transmission electron microscopy investigation of GaAs/(In,Ga)As core-shell nanowires. *Applied Physics Letters*, **2014**, 105, 121602	3.4	14
178	Epitaxial polymorphism of La2O3 on Si(111) studied by in situ x-ray diffraction. *Applied Physics Letters*, **2014**, 105, 021601	3.4	7
177	Microstructure of Group III-N Nanowires **2014**, 125-156		1
176	Epitaxial Fe3Si/Ge/Fe3Si thin film multilayers grown on GaAs(001). *Thin Solid Films*, **2014**, 556, 120-124	2.2	16
175	Control over the number density and diameter of GaAs nanowires on Si(111) mediated by droplet epitaxy. *Nano Letters*, **2013**, 13, 3607-13	11.5	40
174	Nanoscale imaging of InN segregation and polymorphism in single vertically aligned InGaN/GaN multi quantum well nanorods by tip-enhanced Raman scattering. *Nano Letters*, **2013**, 13, 3205-12	11.5	32
173	In situ doping of catalyst-free InAs nanowires with Si: Growth, polytypism, and local vibrational modes of Si. *Applied Physics Letters*, **2013**, 103, 143121	3.4	12

172	GaAs-FeSi core-shell nanowires: nanobar magnets. *Nano Letters*, **2013**, 13, 6203-9	11.5	13
171	Mono- and few-layer nanocrystalline graphene grown on Al2O3(0 0 0 1) by molecular beam epitaxy. *Carbon*, **2013**, 56, 339-350	10.4	51
170	Coherent GdN clusters in epitaxial GaN:Gd thin films determined by transmission electron microscopy. *Nanotechnology*, **2013**, 24, 255701	3.4	6
169	Electron channeling contrast imaging studies of nonpolar nitrides using a scanning electron microscope. *Applied Physics Letters*, **2013**, 102, 142103	3.4	15
168	Oxygen-Deficient Oxide Growth by Subliming the Oxide Source Material: The Cause of Silicide Formation in Rare Earth Oxides on Silicon. *Crystal Growth and Design*, **2013**, 13, 3645-3650	3.5	10
167	Monolithic integration of InGaN segments emitting in the blue, green, and red spectral range in single ordered nanocolumns. *Applied Physics Letters*, **2013**, 102, 181103	3.4	35
166	Selective area growth and characterization of GaN nanocolumns, with and without an InGaN insertion, on semi-polar (11$\bar{2}$2) GaN templates. *Applied Physics Letters*, **2013**, 103, 241905	3.4	14
165	Selective area growth of In(Ga)N/GaN nanocolumns by molecular beam epitaxy on GaN-buffered Si(111): from ultraviolet to infrared emission. *Nanotechnology*, **2013**, 24, 175303	3.4	48
164	Spontaneous nucleation and growth of GaN nanowires: the fundamental role of crystal polarity. *Nano Letters*, **2012**, 12, 6119-25	11.5	103
163	Direct experimental determination of the spontaneous polarization of GaN. *Physical Review B*, **2012**, 86,	3.3	82
162	Scaling growth kinetics of self-induced GaN nanowires. *Applied Physics Letters*, **2012**, 100, 153101	3.4	57
161	Strain accommodation in Ga-assisted GaAs nanowires grown on silicon (111). *Nanotechnology*, **2012**, 23, 305703	3.4	30
160	Epitaxial phase-change materials. *Physica Status Solidi - Rapid Research Letters*, **2012**, 6, 415-417	2.5	29
159	Residual disorder and diffusion in thin Heusler alloy films. *Physical Review B*, **2012**, 86,	3.3	6
158	Critical role of two-dimensional island-mediated growth on the formation of semiconductor heterointerfaces. *Physical Review Letters*, **2012**, 109, 126101	7.4	32
157	Quantitative description for the growth rate of self-induced GaN nanowires. *Physical Review B*, **2012**, 85,	3.3	69
156	Scaling thermodynamic model for the self-induced nucleation of GaN nanowires. *Physical Review B*, **2012**, 85,	3.3	48
155	Delayed crystallization of ultrathin Gd2O3 layers on Si(111) observed by in situ X-ray diffraction. *Nanoscale Research Letters*, **2012**, 7, 203	5	10

154	Current path in light emitting diodes based on nanowire ensembles. *Nanotechnology*, **2012**, 23, 465301	3.4	47
153	E-beam nano-patterning for the ordered growth of GaN/InGaN nanorods. *Microelectronic Engineering*, **2012**, 98, 374-377	2.5	3
152	Atomic interface structure of bixbyite rare-earth sesquioxides grown epitaxially on Si(1 1 1). *Journal Physics D: Applied Physics*, **2012**, 45, 295302	3	2
151	Formation of a Monocrystalline, M-Plane AlN Layer by the Nitridation of $gamma$-LiAlO$_{2}$(100). *Applied Physics Express*, **2012**, 5, 105501	2.4	5
150	Interface properties of (In,Ga)As/GaAs quantum wells grown by solid-phase epitaxy. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 02B108	1.3	4
149	Strain-induced composition limitation in nitrogen □doped (In,Ga)As/GaAs quantum wells. *Applied Physics Letters*, **2012**, 100, 171906	3.4	4
148	ORDERED GAN/INGAN NANORODS ARRAYS GROWN BY MOLECULAR BEAM EPITAXY FOR PHOSPHOR-FREE WHITE LIGHT EMISSION. *International Journal of High Speed Electronics and Systems*, **2012**, 21, 1250010	0.5	7
147	Plasmon excitation in electron energy-loss spectroscopy for determination of indium concentration in (In,Ga)N/GaN nanowires. *Nanotechnology*, **2012**, 23, 485701	3.4	31
146	Selective area growth and characterization of InGaN nano-disks implemented in GaN nanocolumns with different top morphologies. *Applied Physics Letters*, **2012**, 100, 231906	3.4	33
145	Formation of High-Quality GaN Microcrystals by Pendeoepitaxial Overgrowth of GaN Nanowires on Si(111) by Molecular Beam Epitaxy. *Crystal Growth and Design*, **2011**, 11, 4257-4260	3.5	27
144	Macro- and micro-strain in GaN nanowires on Si(111). *Nanotechnology*, **2011**, 22, 295714	3.4	58
143	N-face GaN nanorods: Continuous-flux MOVPE growth and morphological properties. *Journal of Crystal Growth*, **2011**, 315, 164-167	1.6	41
142	Understanding the selective area growth of GaN nanocolumns by MBE using Ti nanomasks. *Journal of Crystal Growth*, **2011**, 325, 89-92	1.6	87
141	The nanorod approach: GaN NanoLEDs for solid state lighting. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2296-2301		114
140	Insight into the Growth and Control of Single-Crystal Layers of Ge□Sb□Te Phase-Change Material. *Crystal Growth and Design*, **2011**, 11, 4606-4610	3.5	33
139	Atomic Configuration of the MnAs/GaAs (110) Interface Analyzed by High-Resolution Electron Microscopy. *Journal of Physical Chemistry C*, **2011**, 115, 529-533	3.8	1
138	Effect of indium incorporation on optical and structural properties of m-plane InGaN/GaN MQW on LiAlO2 substrates. *Journal of Crystal Growth*, **2011**, 315, 246-249	1.6	12
137	Distribution of Mn in ferromagnetic (In,Mn)Sb films grown on (001) GaAs using MBE. *Journal of Crystal Growth*, **2011**, 323, 340-343	1.6	

136	Interface engineering for improved growth of GaSb on Si(111). *Journal of Crystal Growth*, **2011**, 323, 401-404	1.6	23
135	Rare-earth oxide superlattices on Si(1 1 1). *Journal of Crystal Growth*, **2011**, 323, 95-98	1.6	4
134	Monodisperse (In, Ga)N insertions in catalyst-free-grown GaN(0001) nanowires. *Nanotechnology*, **2011**, 22, 365703	3.4	14
133	Polarity determination by electron energy-loss spectroscopy: application to ultra-small III-nitride semiconductor nanocolumns. *Nanotechnology*, **2011**, 22, 415701	3.4	27
132	Direct observation of N-(group V) bonding defects in dilute nitride semiconductors using hard x-ray photoelectron spectroscopy. *Applied Physics Letters*, **2011**, 98, 121915	3.4	10
131	Emission control of InGaN nanocolumns grown by molecular-beam epitaxy on Si(111) substrates. *Applied Physics Letters*, **2011**, 99, 131108	3.4	28
130	Long-range order and thermal stability of thin Co2FeSi films on GaAs(1 1 1)B. *Journal Physics D: Applied Physics*, **2010**, 43, 285404	3	6
129	Epitaxial growth and structure of (La1−xLux)2O3 alloys on Si(111). *Applied Physics Letters*, **2010**, 97, 031911	3.4	13
128	Epitaxial Heusler alloy Co2FeSi films on Si(1 1 1) substrates grown by molecular beam epitaxy. *Journal Physics D: Applied Physics*, **2010**, 43, 305004	3	11
127	Continuous-flux MOVPE growth of position-controlled N-face GaN nanorods and embedded InGaN quantum wells. *Nanotechnology*, **2010**, 21, 305201	3.4	126
126	In situ analysis of strain relaxation during catalyst-free nucleation and growth of GaN nanowires. *Nanotechnology*, **2010**, 21, 245705	3.4	38
125	Striated surface morphology and crystal orientation of m-plane GaN films grown on □-LiAlO2(100). *Applied Physics Letters*, **2010**, 96, 231914	3.4	14
124	Collector phase transitions during vapor-solid-solid nucleation of GaN nanowires. *Nano Letters*, **2010**, 10, 3426-31	11.5	44
123	Morphology and stress evolution of InAs QD grown and annealed in-situ at high temperature. *Journal of Crystal Growth*, **2010**, 312, 447-451	1.6	9
122	1.3 □m emitting GaInNAs/GaAs quantum well resonant cavity LEDs. *Solid-State Electronics*, **2010**, 54, 492-496	1.6	6
121	Anisotropic properties of MOVPE-grown m-plane GaN layers on LiAlO2 substrates. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1750-1752	1.3	2
120	GaN and ZnO nanostructures. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 2315-2328	1.3	4
119	InN nanocolumns grown by plasma-assisted molecular beam epitaxy on A-plane GaN templates. *Applied Physics Letters*, **2009**, 94, 221908	3.4	9

118	Metal-organic vapour-phase epitaxy of gallium nitride nanostructures for optoelectronic applications. *Microelectronics Journal*, **2009**, 40, 333-335	1.8	4
117	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2009**, 311, 1739-1744	1.6	21
116	The role of Sb and N ions on the morphology and localization of (Ga,In) (N,As) quantum wells. *Journal of Crystal Growth*, **2009**, 311, 1728-1732	1.6	3
115	Carrier spin polarization in ferromagnet□semiconductor (Ga,Mn)As/GaAs structures. *Journal of Magnetism and Magnetic Materials*, **2009**, 321, 720-722	2.8	3
114	Effects of nanowire coalescence on their structural and optical properties on a local scale. *Applied Physics Letters*, **2009**, 95, 241910	3.4	80
113	Ge(1-x) Mn(x) clusters: central structural and magnetic building blocks of nanoscale wire-like self-assembly in a magnetic semiconductor. *Nano Letters*, **2009**, 9, 3743-8	11.5	33
112	. *IEEE Journal of Selected Topics in Quantum Electronics*, **2008**, 14, 1188-1196	3.8	20
111	Gallium nitride heterostructures on 3D□structured silicon. *Nanotechnology*, **2008**, 19, 405301	3.4	10
110	Indium distribution at the interfaces of (Ga,In)(N,As)□GaAs quantum wells. *Applied Physics Letters*, **2008**, 92, 141913	3.4	21
109	Linear increase of the modal gain in 1.3□μm InAs/GaAs quantum dot lasers containing up to seven-stacked QD layers. *Nanotechnology*, **2008**, 19, 275401	3.4	11
108	Impact of carrier localization on the photoluminescence characteristics of (Ga,In)(N,As) and (Ga,In)(N,As,Sb) quantum wells. *Journal of Applied Physics*, **2008**, 104, 113502	2.5	14
107	Type II transition in InSb-based nanostructures for midinfrared applications. *Journal of Applied Physics*, **2008**, 103, 114516	2.5	9
106	On the mechanisms of spontaneous growth of III-nitride nanocolumns by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2008**, 310, 4035-4045	1.6	150
105	Vertical composition fluctuations in (Ga,In)(N,As) quantum wells grown on vicinal (111)B GaAs. *Journal of Physics and Chemistry of Solids*, **2008**, 69, 343-346	3.9	2
104	Composition fluctuations and clustering in (Ga,In)(N,As)/GaAs(001) heterostructures studied by analytical transmission electron microscopy. *Journal of Physics and Chemistry of Solids*, **2008**, 69, 335-342	3.9	3
103	Epitaxial growth of 6H-AlN on M-plane SiC by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2007**, 300, 127-129	1.6	14
102	Interface analysis of InAs/GaSb superlattice grown by MBE. *Journal of Crystal Growth*, **2007**, 301-302, 889-892	1.6	42
101	Growth of (In,Ga)As/(Al,Ga)As quantum wells on GaAs(1 1 0) by MBE. *Journal of Crystal Growth*, **2007**, 301-302, 158-162	1.6	7

100	Growth of freestanding GaN using pillar-epitaxial lateral overgrowth from GaN nanocolumns. *Journal of Crystal Growth*, **2007**, 309, 113-120	1.6	31
99	Inelastic light scattering spectroscopy of semiconductor nitride nanocolumns. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 2838-2846	1.3	4
98	MBE growth and interface formation of compound semiconductor heterostructures for optoelectronics. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 2683-2696	1.3	9
97	Growth, morphology, and structural properties of group-III-nitride nanocolumns and nanodisks. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 2816-2837	1.3	142
96	InAs/GaSb short-period superlattice injection lasers operating in 2.5 [micro sign]m3.5 [micro sign]m mid-infrared wavelength range. *Electronics Letters*, **2007**, 43, 1285	1.1	12
95	Role of ionized nitrogen species in the optical and structural properties of GaInNAs/GaAs quantum wells grown by plasma-assisted molecular beam epitaxy. *Journal of Applied Physics*, **2007**, 101, 103526	2.5	8
94	Molecular-beam epitaxy of InSb/GaSb quantum dots. *Journal of Applied Physics*, **2007**, 101, 124309	2.5	28
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